WGM100PC120T1

1200V，100A three-phase PIM IGBT Module with Trench Field Stop technology .The Power Integrated module with integration of rectifier and brake chopper.

Features：

- Trench-FS IGBT
- Low $V_{CE\ set}$
- Low Switching Loss
- Low L_S
- Tj max=175 ℃
- 100%RBSOA Tested（2Ic）
- $V_{CE\ set}$ with positive temp. coefficient
- RoHS

Applications:

- Motor Drives
- Servo Drives

Maximum Rated Valued of IGBT,Inverter

集电极-发射极电压 Collector-emitter voltage	V_{CES}	T_J=25℃	1200	V
栅极-发射极峰值电压 Gate-emitter peak voltage	V_{GES}		±20	V
连续集电极电流 Continuous collector current	I_C	Tc=100℃ Tc=25℃	100 200	A
集电极重复峰值电流 Repetitive peak collector current	I_{CM}	T_J=175℃，t_P=1ms	200	A
最大损耗功率 Maximum power dissipation per IGBT	P_D	Tc=25℃ $T_{J\ max}$=175℃	714	W

Electrical Characteristics of IGBT,Inverter

				Min.	Typ.	Max.	
集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{CE\ sat}$	I_C=100A，V_{GE}=15V	T_J=25℃ T_J=125℃ T_J=150℃		1.7 1.9 1.9	2.0	V V V
栅极阈值电压 Gate threshold voltage	$V_{GE(th)}$	I_C=1mA，V_{CE}=VGE，	T_J=25℃	5.0	5.5	6.6	V
栅极电荷 Gate charge	Q_G	V_{GE} = -15 V ... +15 V	T_J=25℃		0.75		uC
内部栅极电阻 Internal gate resistor	R_{Gint}		T_J=25℃		7.5		Ω
输入电容 Input capacitance	C_{ies}	f=1MHz，V_{CE}=25V，V_{GE}=0V	T_J=25℃		8.03		nF
反向传输电容 Reverse transfer capacitance	C_{res}	f=1MHz，V_{CE}=25V，V_{GE}=0V	T_J=25℃		1.22		nF
集电极-发射极截止电流 Collector-emitter cut-off current	I_{CES}	V_{CE}=1200V，V_{GE}=0V	T_J=25℃			1	mA
栅极-发射极漏电流 Gate-emitter leakage current	I_{GES}	V_{CE}=0V，V_{GE}=±20V	T_J=25℃			200	nA
开通延迟时间（电感负载） Turn-on delay time	$t_{d\ on}$	V_{CC}=600V，I_C=100A，R_{Gon}=1Ω， V_{GE}=±15V	T_J=25℃ T_J=125℃ T_J=150℃		228 250 254		ns ns ns
上升时间（电感负载） Rise time	t_r	V_{CC}=600V，I_C=100A，R_{Gon}=1Ω， V_{GE}=±15V	T_J=25℃ T_J=125℃ T_J=150℃		63 67 69		ns ns ns
关断延迟时间（电感负载） Turn-off delay time	$t_{d\ off}$	V_{CC}=600V，I_C=100A，R_{Goff}=1Ω， V_{GE}=±15V	T_J=25℃ T_J=125℃ T_J=150℃		269 279 284		ns ns ns
下降时间（电感负载） Fall time	t_f	V_{CC}=600V，I_C=100A，R_{Goff}=1Ω， V_{GE}=±15V	T_J=25℃ T_J=125℃ T_J=150℃		184 291 317		ns ns ns
开通损耗能量（电感负载） Turn-on energy loss per pulse	E_{on}	V_{CC}=600V，I_C=100A，R_{Gon}=1Ω， V_{GE}=±15V di/dt=1387A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		3.1 4.3 4.8		mJ mJ mJ
关断损耗能量（电感负载） Turn-off energy loss per pulse	E_{off}	V_{CC}=600V，I_C=100A，R_{Goff}=1Ω， V_{GE}=±15V du/dt=4448V/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		5.28 8.33 9.3		mJ mJ mJ
短路数据 SC data	I_{SC}	$V_{GE=\pm}$15V，V_{CC}=600V，R_G=1Ω， t_P=10us	T_J=25℃		575		A
结-外壳热阻 Thermal resistance，junction to case	$R_{th\ JC}$	per leg			0.21		K/W

Maximum Rated Valued of Diode,Inverter

反向重复峰值电压 Repetitive peak reverse voltage	V_{RRM}		T_C=25℃	1200	V
正向连续电流 continuous forward current	I_F		T_C=25℃	100	A
正向峰值电流 Maximum forward voltage	I_{FM}	t_P=1ms	T_C=25℃	200	A

Electrical Characteristics of Diode,Inverter

				Min.	Typ.	Max.	
正向电压 Forward voltage	V_F	I_F=100A	T_J=25℃ T_J=125℃ T_J=150℃		1.70 1.80 1.80		V V V
反向恢复峰值电流 Peak reverse recovery current	I_{RM}	V_R=600V，I_F=100A，V_{GE}=-15V -di/dt=1911A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		92 104 105		A A A
反向恢复时间 Reverse recovery time	t_{rr}	V_R=600V，I_F=100A，V_{GE}=-15V -di/dt=1911A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		260 396 454		ns ns ns
反向恢复电荷 Reverse Recovery charge	Q_r	V_R=600V，I_F=100A，V_{GE}=-15V -di/dt=1911A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		10.2 16.8 19.2		uC uC uC
反向恢复损耗（每脉冲） Reverse recovery energy	E_{rec}	V_R=600V，I_F=100A，V_{GE}=-15V -di/dt=1911A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		4.83 7.92 9.13		mJ mJ mJ
结-外壳热阻 Thermal resistance，junction to case	$R_{th\ JC}$	per leg			0.34		K/W

Maximum Rated Valued of IGBT,Brake-Chopper

集电极-发射极电压 Collector-emitter voltage	V_{CES}	T_J=25℃	1200	V
栅极-发射极峰值电压 Gate-emitter peak voltage	V_{GES}		±20	V
连续集电极电流 Continuous collector current	I_C	Tc=100℃ Tc=25℃	50 100	A
集电极重复峰值电流 Repetitive peak collector current	I_{CM}	T_J=150℃，t_P=1ms	100	A
最大损耗功率 Maximum power dissipation per IGBT	P_D	Tc=25℃ $T_{J\ max}$=175℃	398	W

Electrical Characteristics of IGBT, Brake-Chopper

				Min.	Typ.	Max.	
集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{CE\ sat}$	I_C=50A，V_{GE}=15V	T_J=25℃ T_J=125℃ T_J=150℃		1.7 1.9 1.9	2.0	V V V
栅极阈值电压 Gate threshold voltage	$V_{GE(th)}$	I_C=1mA，V_{CE}=VGE，	T_J=25℃	5.0	5.5	6.6	V
栅极电荷 Gate charge	Q_G	V_{GE} = -15 V ... +15 V	T_J=25℃		0.51		uC
内部栅极电阻 Internal gate resistor	R_{Gint}		T_J=25℃		4		Ω
输入电容 Input capacitance	C_{ies}	f=1MHz，V_{CE}=25V，V_{GE}=0V	T_J=25℃		3.65		nF
反向传输电容 Reverse transfer capacitance	C_{res}	f=1MHz，V_{CE}=25V，V_{GE}=0V	T_J=25℃		0.5		nF
集电极-发射极截止电流 Collector-emitter cut-off current	I_{CES}	V_{CE}=1200V，V_{GE}=0V	T_J=25℃			1	mA
栅极-发射极漏电流 Gate-emitter leakage current	I_{GES}	V_{CE}=0V，V_{GE}=±20V	T_J=25℃			100	nA
开通延迟时间（电感负载） Turn-on delay time	$t_{d\ on}$	V_{CC}=600V，I_C=50A，R_{Gon}=15Ω， V_{GE}=±15V	T_J=25℃ T_J=125℃ T_J=150℃		154 169 174		ns ns ns
上升时间（电感负载） Rise time	t_r	V_{CC}=600V，I_C=50A，R_{Gon}=15Ω， V_{GE}=±15V	T_J=25℃ T_J=125℃ T_J=150℃		51 54 56		ns ns ns
关断延迟时间（电感负载） Turn-off delay time	$t_{d\ off}$	V_{CC}=600V，I_C=50A，R_{Goff}=15Ω， V_{GE}=±15V	T_J=25℃ T_J=125℃ T_J=150℃		202 216 225		ns ns ns
下降时间（电感负载） Fall time	t_f	V_{CC}=600V，I_C=50A，R_{Goff}=15Ω， V_{GE}=±15V	T_J=25℃ T_J=125℃ T_J=150℃		220 379 407		ns ns ns
开通损耗能量（电感负载） Turn-on energy loss per pulse	E_{on}	V_{CC}=600V，I_C=50A，R_{Gon}=15Ω， V_{GE}=±15V di/dt=791A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		3.37 5.1 5.53		mJ mJ mJ
关断损耗能量（电感负载） Turn-off energy loss per pulse	E_{off}	V_{CC}=600V，I_C=50A，R_{Goff}=15Ω， V_{GE}=±15V du/dt=3488V/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		2.42 4.09 4.52		mJ mJ mJ
短路数据 SC data	I_{SC}	$V_{GE=\pm}$15V，V_{CC}=600V，R_G=15Ω， t_P=10us	T_J=25℃		297		A
结-外壳热阻 Thermal resistance，junction to case	$R_{th\ JC}$	per leg			0.38		K/W

Maximum Rated Valued of Diode, Brake-Chopper

反向重复峰值电压 Repetitive peak reverse voltage	V_{RRM}		T_C=25℃	1200	V
正向连续电流 continuous forward current	I_F		T_C=25℃	35	A
正向峰值电流 Maximum forward voltage	I_{FM}	t_P=1ms	T_C=25℃	70	A

Electrical Characteristics of Diode, Brake-Chopper

				Min.	Typ.	Max.	
正向电压 Forward voltage	V_F	I_F=35A	T_J=25℃ T_J=125℃ T_J=150℃		2.0 2.1 2.1	2.2	V V V
反向恢复峰值电流 Peak reverse recovery current	I_{RM}	V_R=600V，I_F=35A，V_{GE}=-15V -di/dt=590A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		15.1 19.2 20.6		A A A
反向恢复时间 Reverse recovery time	t_{rr}	V_R=600V，I_F=35A，V_{GE}=-15V -di/dt=590A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		320 450 480		ns ns ns
反向恢复电荷 Reverse Recovery charge	Q_r	V_R=600V，I_F=35A，V_{GE}=-15V -di/dt=590A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		1.8 3.5 4.2		uC uC uC
反向恢复损耗（每脉冲） Reverse recovery energy	E_{rec}	V_R=600V，I_F=35A，V_{GE}=-15V -di/dt=590A/us（T_J=150℃）	T_J=25℃ T_J=125℃ T_J=150℃		0.5 1.2 1.6		mJ mJ mJ
结-外壳热阻 Thermal resistance，junction to case	$R_{th\ JC}$	per leg			0.65		K/W

Maximum Rated Valued of Diode, Rectifier

反向重复峰值电压 Repetitive peak reverse voltage	V_{RRM}		T_J=25℃	1800	V
最大正向均方根电流 Maximum RMS forward current	I_{FRMSM}	per chip	T_J=80℃	130	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	I_{RMSM}		T_J=80℃	180	A
正向浪涌电流 Surge forward current	I_{FSM}	t_P=10ms	T_J=25℃ T_J=150℃	1500 1150	A
I^2t I^2t-Value	I^2t	t_P=10ms	T_J=25℃ T_J=150℃	11560 6610	A^2s

Electrical Characteristics of Diode, Rectifier

				Min.	Typ.	Max.	
正向电压 Forward voltage	V_F	I_F=85A	T_J=25℃ T_J=125℃ T_J=150℃		1.0 0.9 0.9		V V V
反向恢复峰值电流 Reverse current	I_R	V_R=1800V	T_J=25℃			1	mA
结-外壳热阻 Thermal resistance，junction to case	$R_{th\ JC}$	per leg			0.29		K/W

NTC-Thermistor

额定电阻值 Rated resistance	R_{25}	Tc=25℃		5		KΩ
R100 偏差 Deviation of R100	△R/R	Tc=100℃，R100=481Ω			±5	%
耗散功率 Power dissipation	P25	Tc=25℃		50		mW
B-值 B-Value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3380		K
B-值 B-Value	$B_{25/80}$	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15K))]$		3440		K

Module

			Min.	Typ.	Max.	
绝缘电压 Isolation voltage	V_{ISO}	f=50Hz，t=1min，RMS，All terminals shorted	2500			V
模块寄生电感 Stray Inductance Module	Ls			40		nH
相对电痕指数 Comparative tracking index	CTI		200			V
最高结温 Maximum junction temperature	$T_{J\ max}$		-40		175	℃
工作结温 Operating junction temperature	$T_{J\ OP}$		-40		150	℃
储存温度 Storage temperature	T_{stg}		-40		125	℃
外壳-散热器热阻 Thermal resistance，case to heatsink	R_{thCH}	Thermal grease applied		0.10		K/W
安装扭矩 Mounting torque	T	Mounting screw：M5	3.0		5.0	N·m N·m
重量 Weight	G			300		g

Fig.1 Typical saturation voltage characteristics vs temp.
IGBT，Inverter

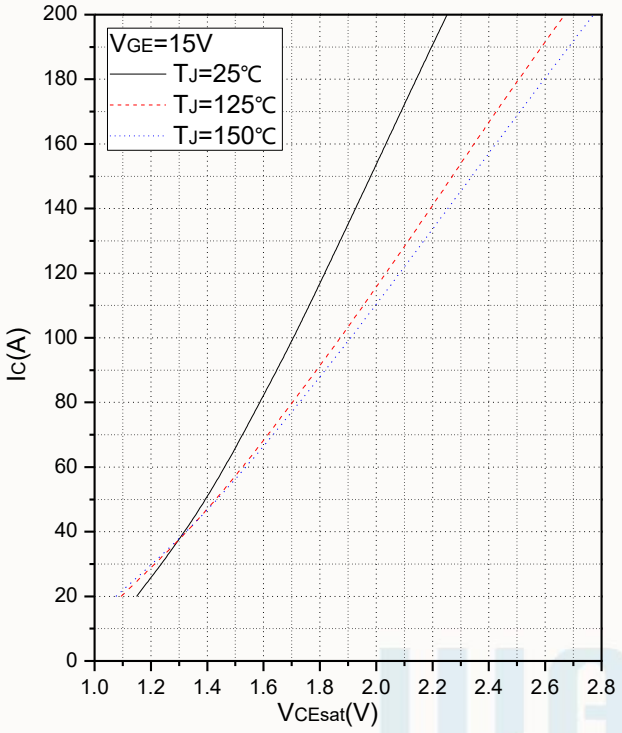


Fig.2 Typical output characteristics vs V_{GE}
IGBT，Inverter

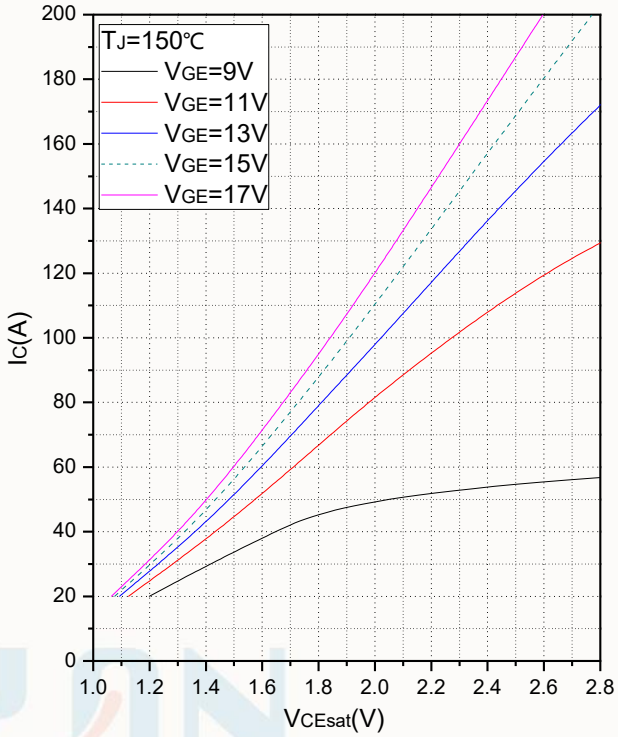


Fig.3 Transfer Characteristic VS V_{GE}
IGBT，Inverter

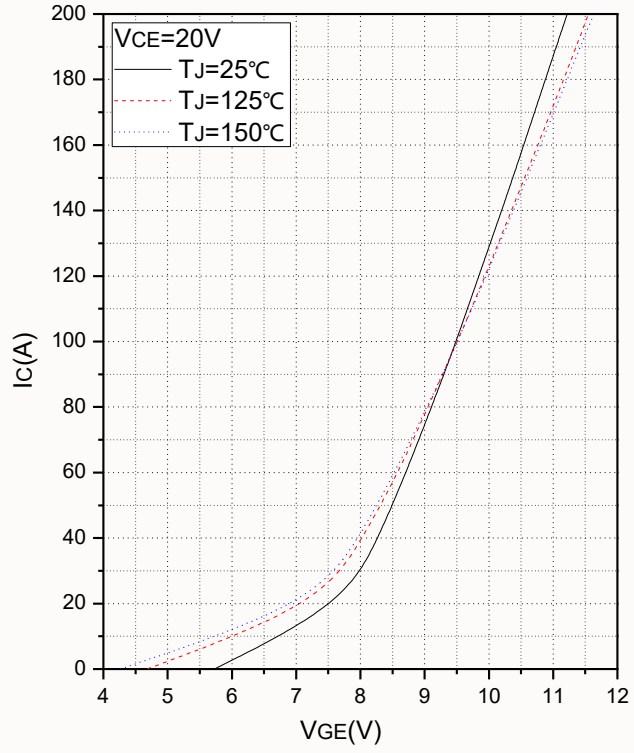


Fig.4 Typical switching loss vs Collector current
IGBT，Inverter

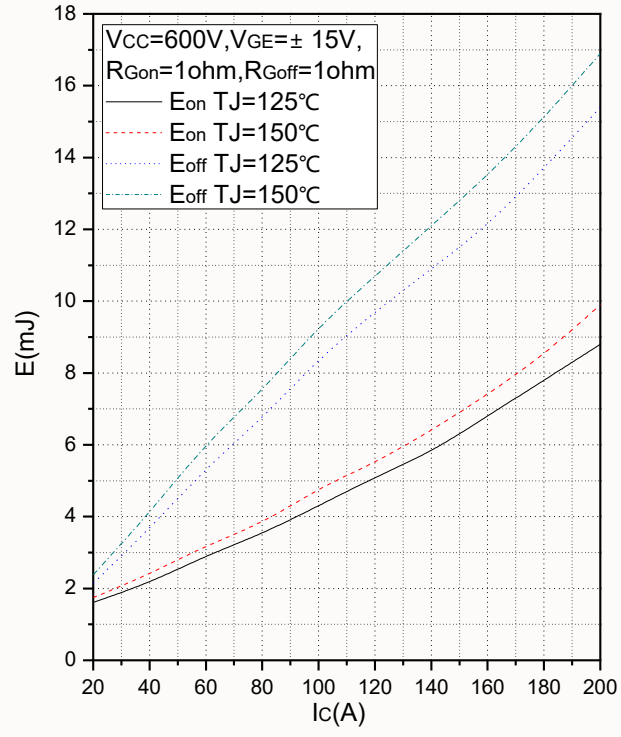


Fig.5 Typical switching loss vs Gate resistance
IGBT, Inverter

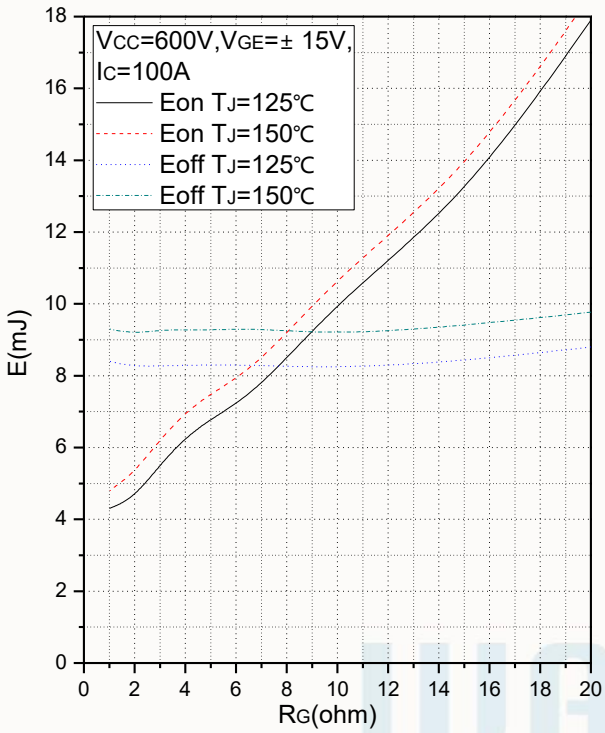


Fig.6 Transient thermal impedance
IGBT, Inverter

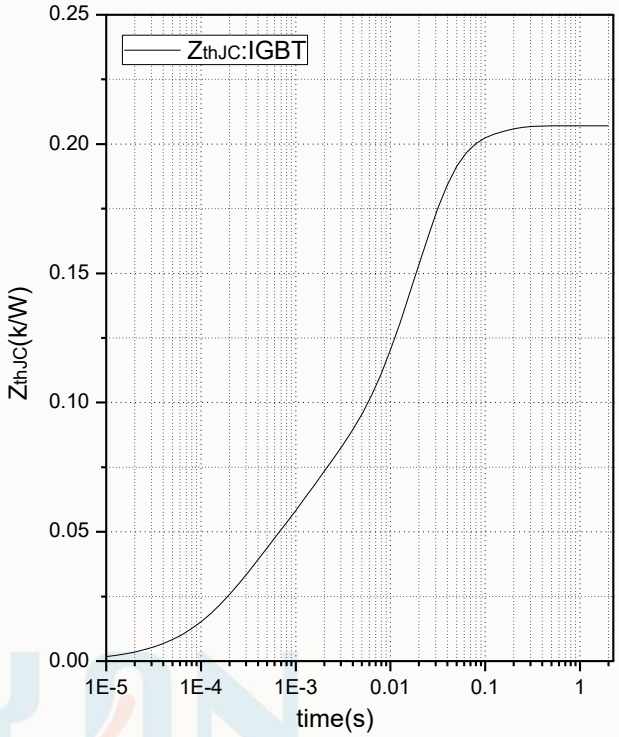


Fig.7 Capacitance Characteristics
IGBT, Inverter

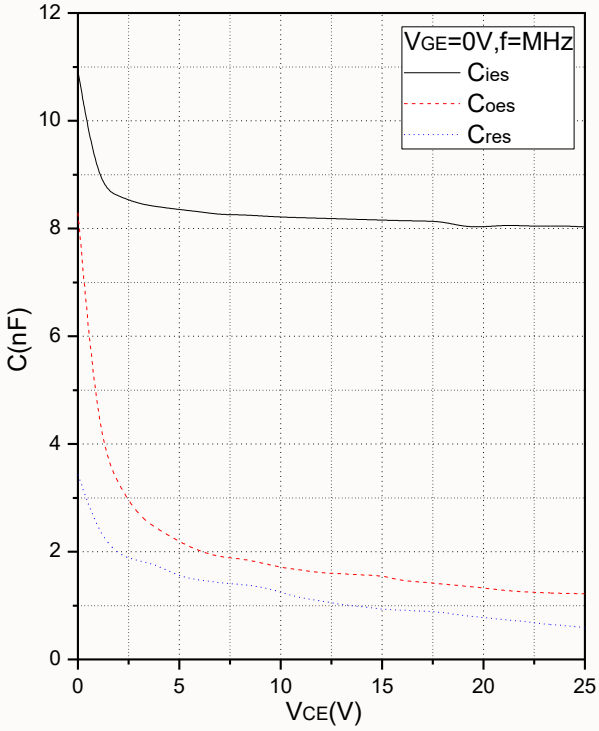


Fig.8 Typical forward characteristic
Diode, Inverter

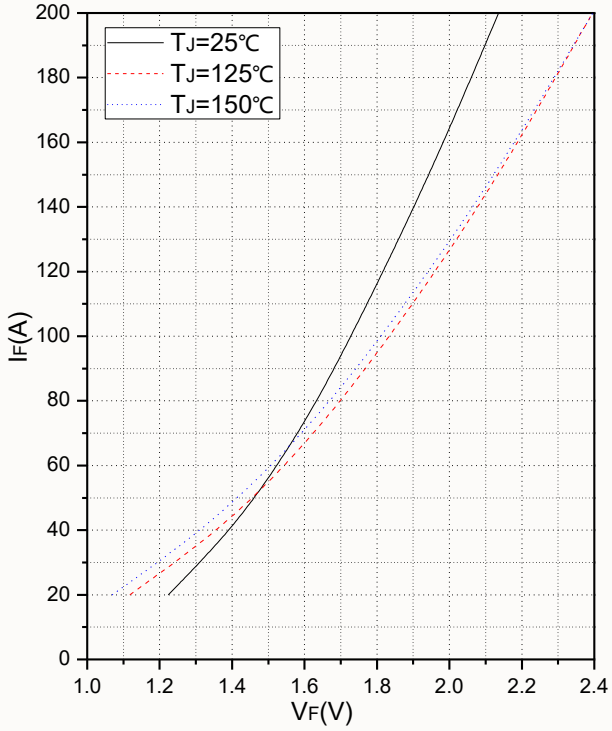


Fig.9 Typical switching loss vs Forward current
Diode, Inverter

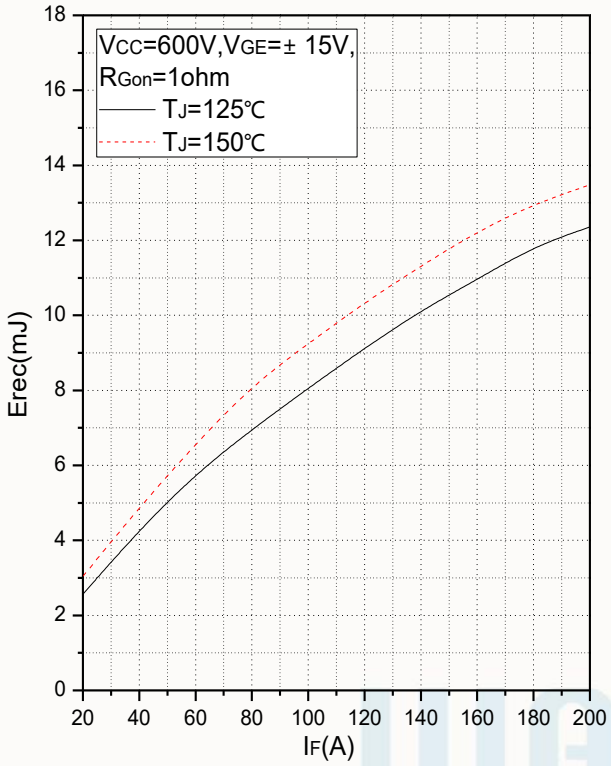


Fig.10 Typical switching loss vs R_G
Diode, Inverter

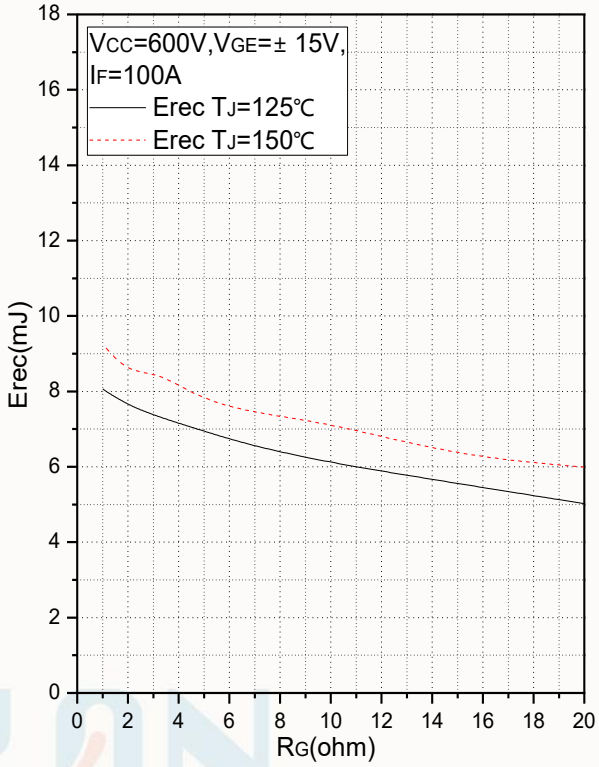


Fig.11 Transient thermal impedance
Diode, Inverter

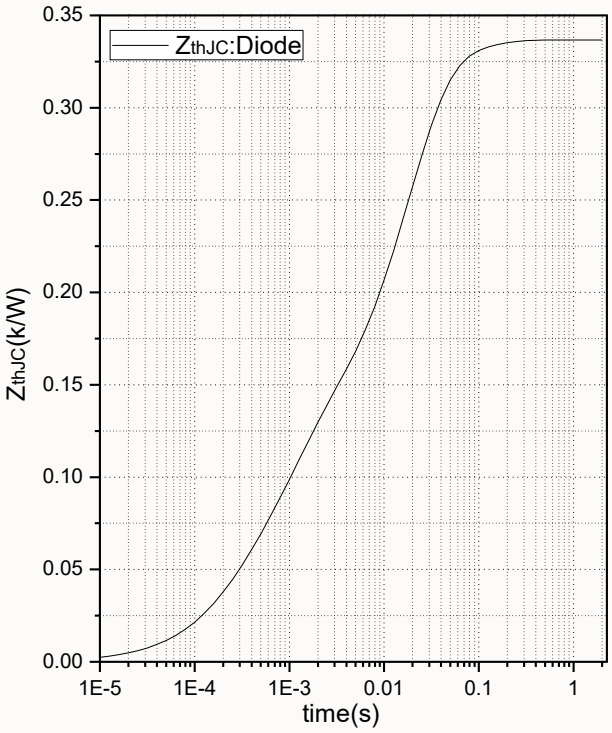


Fig.12 Typical saturation voltage characteristics vs temp.
IGB, Brake-Chopper

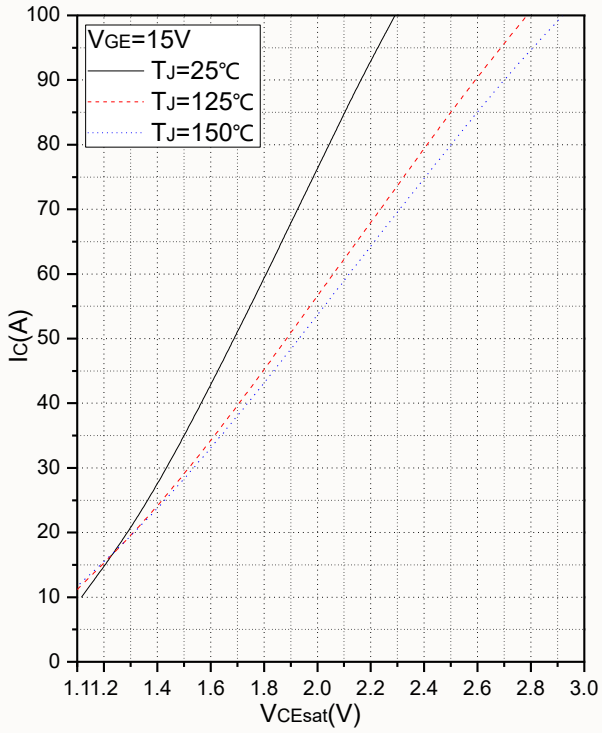


Fig.13 Typical forward characteristic

Diode，Brake-Chopper

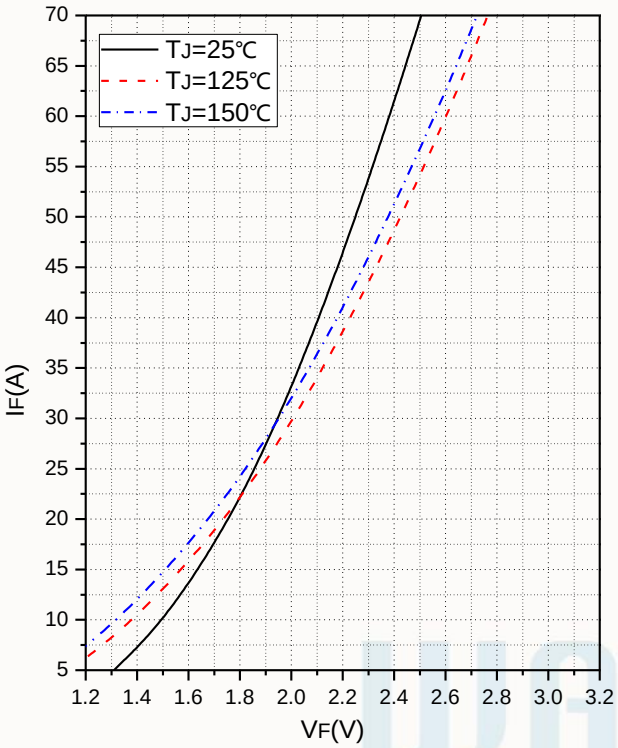


Fig.14 Typical forward characteristic

Diode，Rectifier

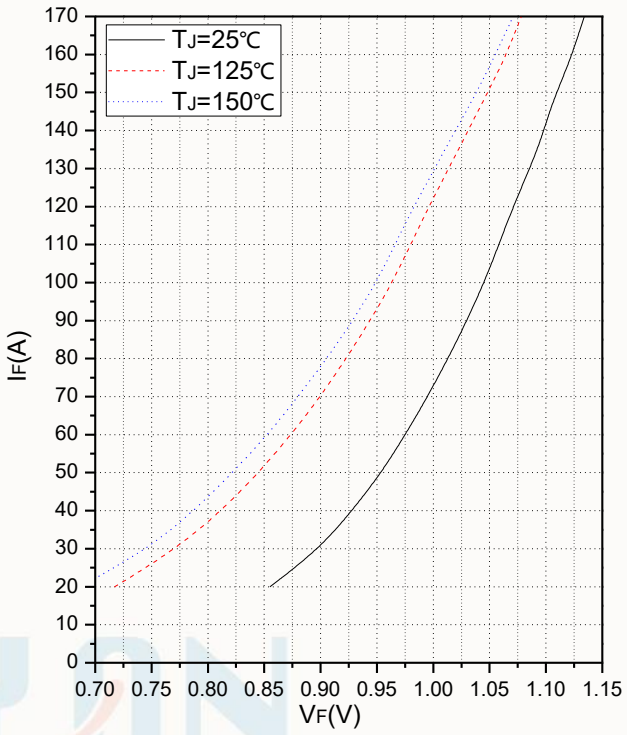


Fig.15 Reverse bias safe operating area (RBSOA)

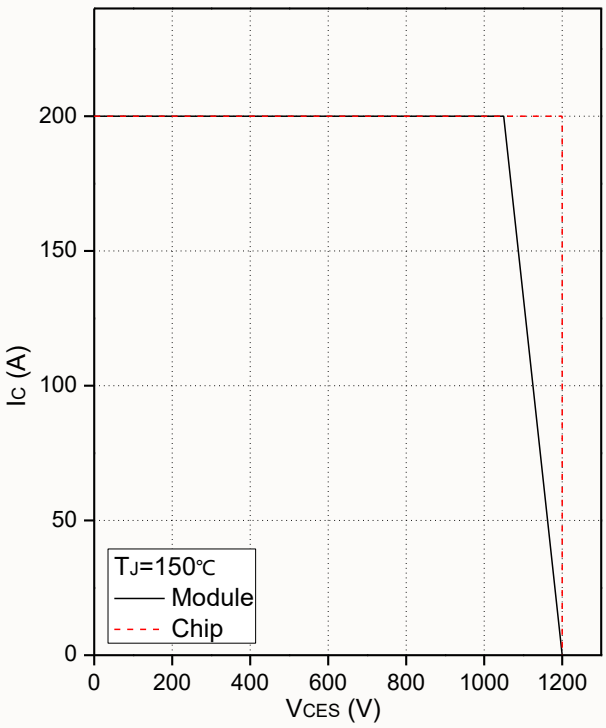
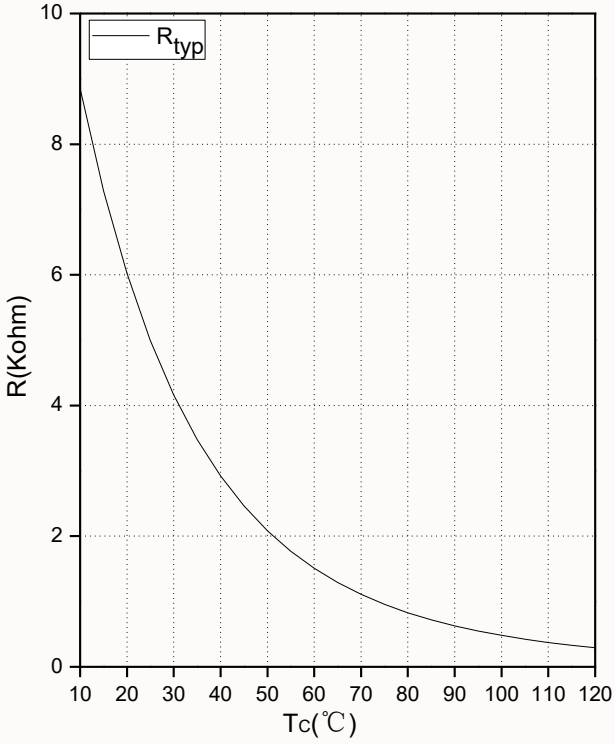
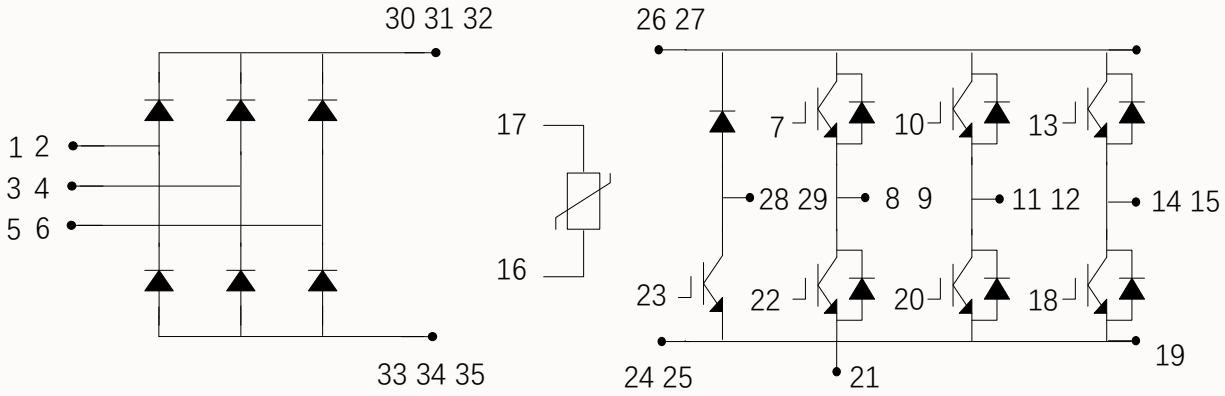


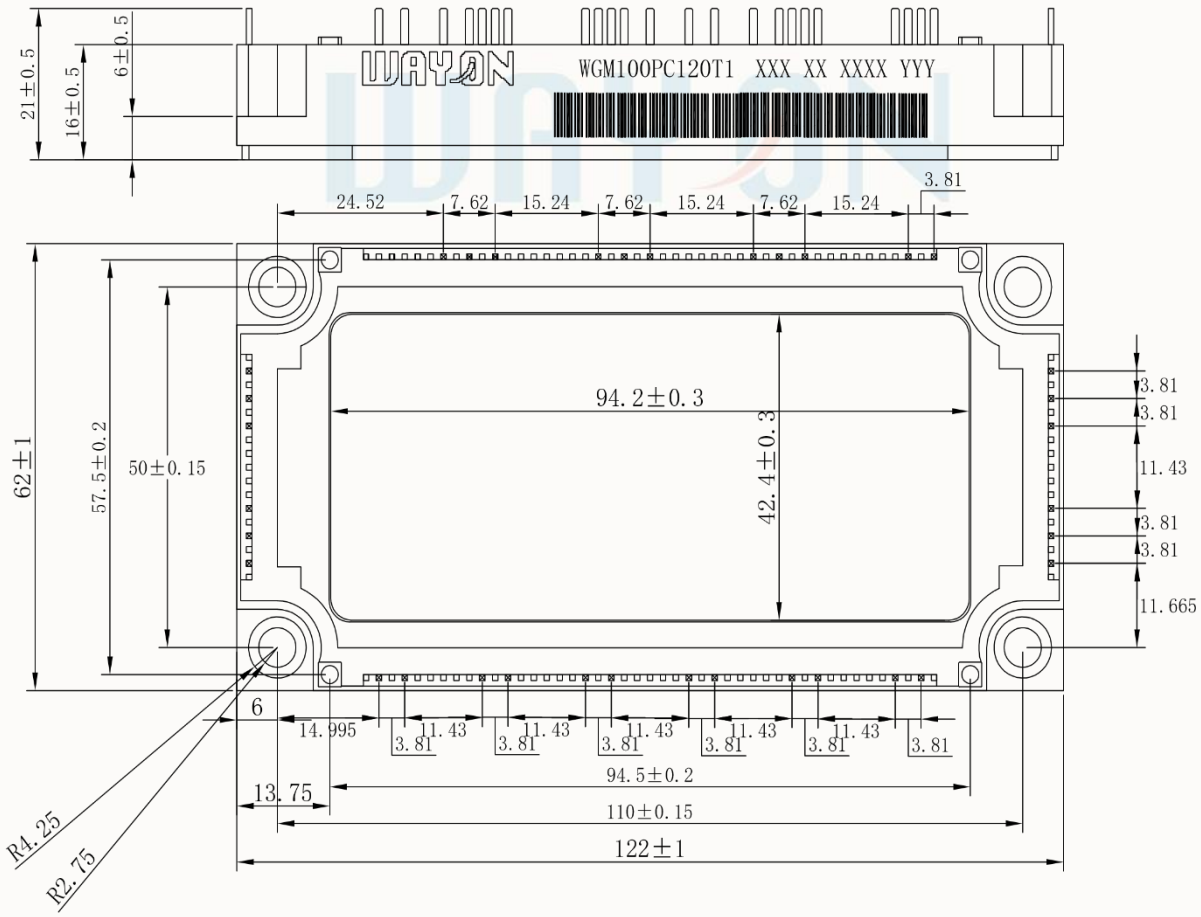
Fig.16 NTC Temperature Characteristics



Internal circuit（接线图）



Package outline（mm）（封装尺寸）



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http://www.way-on.com

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